

## Polysilicon Layers Structure and Method of Forming Same

### ABSTRACT OF THE DISCLOSURE

[41] In accordance with an embodiment of the present invention, a semiconductor structure includes an undoped polysilicon layer, a doped polysilicon layer in contact with the undoped polysilicon layer, and an insulating layer in contact with the undoped polysilicon layer. The undoped polysilicon layer is sandwiched between the doped polysilicon layer and the insulating layer.

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